





Extended X-Ray Absorption Fine Structure

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EXAFS

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1.Interaction of X-rays with matter
 2.Basics aspects about XAFS
 3.Understanding the EXAFS equation





Primary competing processes and some radiative and non-radiative decay processes







 The excess energy of X-rays is transferred to the ejected photoelectron.





- What is XAFS?
 - XAFS studies the details of the x-ray absorption coefficient around an absorption edge.
 - It reveals a wealth of information regarding the geometric and electronic structure of materials.







Main characteristics of XAS technique

- Most atoms of the periodic table can be studied;
- · Selectivity at the atomic level;
- Sensitive to oxidation state, coordination number and interatomic distance kind of atom;
- Structure of amorphous and crystalline materials and highly diluted systems;
- · Solids, liquids and gases can have their specific local structure.
- Different environments (pressure, temperature, magnetic field, gas ...)
- Limitations
- We can not distinguish neighboring atoms in the periodic table;
- Only the local order can be precisely determined;
- A source of X-ray wavelength variable is required.







XAFS: Study the details of the variation on the absorption coefficient (fine structure) after the edge.

$$\begin{array}{ccc} K & 1s \rightarrow p \\ L_1 & 2s \rightarrow p \\ L_2 & 2p_{1/2} \rightarrow s, d \\ L_3 & 2p_{3/2} \rightarrow s, d \end{array}$$





X-ray attenuation

Absorption coefficient:



- μ : linear absorption coefficient
- t : thickness

μt: absorbance

 $I_1 = I_0 \exp(-\mu t)$

Includes contributions from all scattering and absorption precesses

Mass absorpion coefficient:

Atomic absorption coefficient:







Basic XAFS experiment – sequential mode



$$\mu t = \log\left(\frac{I_0}{I_1}\right)$$















The most important criterion: The best signal to noise ratio for the element of interest

Always transmission, if possible Most accurate method, best overall S/N counting statistics of about 10⁻⁴ from beamlines with more than 10⁸ photons/s)

Fluorescence for very diluted samples

A specific signal reduces the large background (but maximum tolerable detector count-rate can result in very long measuring times).

Total electron yield (TEY)

for surface sensitivity and surface XAFS (adsorbates on surfaces) TEY for thick samples that cannot be made uniform.

XEOL X-ray excited optical luminescence VIS/UV detection from luminescent samples







XANES is the region ~50 eV around the edge





XANES : transitions to unoccupied states (localized and continuum)

low energy photoelectron \rightarrow multiple scattering (MS)

Information content

Fermi energy
Projected density of unoccupied states
Oxidation states

- Coordination symmetry

EXAFS: high energy photoelectron \rightarrow single scattering + some important MS

Information content

- interatomic distances
- disorder
- •coordination numbes
- •Bond-angle distributions
- Partial pair distribution
- •Vibrational properties.









XANES: pre edge structure

















 $E \rightarrow$







EXAFS is the region from 50 - 1200 eV after the edge





- •Photon energy $(E\gamma)$ > Binding Energy (E_1) : Photoelectric effect.
- •Kinetic energy of the photoelectron (E_c)= E_{γ} E_L
- •Wave-Particle duality: The photoelectron travel as a esferic wave: $E_c = hv$
- •Wavevector of the photoelectron: K

$$k = \sqrt{\frac{2m_e(E_{\gamma} - E_L)}{\hbar^2}}$$

•Quantical state of the photoelectron: superposition of the propagating wave with the retrodispersed waves on the neightbourgs

•Phase difference of the incoming and outgoing waves: $\Delta \phi$

 $\Delta \varphi \approx 2kR$

•Interference in between propagating waves and retrodispersed ones. This moduls the absorption coefficient.

- •Oscilation frequence: 2R
- •Oscilation amplitudes: number of neightbourgs and disorder













Principal hypothesis:

- Final states are plane waves
- •Gaussian disorder
- Dipolares transitions
- •One active electron
- Photoelectron dispersion is single

Sayers et al., PRL 27, 1204 (1971)

$$\mu(E) \propto \sum_{f}^{E_{f} > E_{F}} \left| \left\langle f \left| \hat{\mathbf{e}} \bullet \vec{r} \right| i \right\rangle \right|^{2} \delta(E_{f})$$

$$\chi(k) = \sum_{i} \frac{N_{i}}{kR_{i}^{2}} S_{0}^{2} F_{i}(k) e^{-2k^{2}\sigma_{i}^{2}} e^{\left[\frac{-2R_{i}}{\lambda}\right]} \sin[2kR_{i} - \phi_{i}(k)]$$

Estructural parameters



Atomic parameters: Absoption and dispersion of the Photoelectron





























CNPEM











 $\chi x \ K^2$

 $\chi \times K^2$

Understanding the XAFS equation









Gaussian Disorder: $\sigma = 0.03$ Å

























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Atomic parameters: Absoption and dispersion of the Photoelectron









Studying a system with one technique is equivalent to studying it with zero techniques

- Bruce Ravel citing anonymous source







Obrigado pela sua atenção!

Questions, please email me: <u>santiago.figueroa@lnls.br</u>

- More info about XAFS:
- https://speakerdeck.com/bruceravel?page=2
- http://cars.uchicago.edu/ifeffit/Mailing_List
- http://xafs.org/Tutorials
- http://www.ixasportal.net/ixas/
- http://cars.uchicago.edu/ifeffit/Documentation
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